

TOSHIBA Semiconductor Lead(Pb)-Free Memory Products

Toshiba America Electronic Components, Inc. Memory Business Unit September 2005

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Announcement of a plan for Lead(Pb)-Free semiconductor products

Dear Customers,

We would like to express our gratitude to our Customers for using Toshiba semiconductor products and announce Toshiba Semiconductor Company's plan to transition to Lead(Pb)-Free semiconductor products.

Awareness of environmental issues has been rapidly increasing as is the adoption of laws and regulations that restrict the use of certain substances in electronic components. We at Toshiba Semiconductor Company have been making efforts to help our customers comply with these various laws and regulations by reducing these restricted substances in production lines. As a part of this effort, we have also developed a fundamental process to produce Lead(Pb)-Free products, which is described in more detail in the attached plan. Many products have already been shifted according to Customers' plans. Toshiba Semiconductor Company is beginning the next phase of its conversion plan, working with customers to gradually convert all memory product shipments to Lead(Pb)-Free, with a goal of completing this transition by the end of 2005.

The conversion of lead(Pb)-contained products to Lead(Pb)-Free products will be implemented gradually in accordance with your plan(s) upon your approval. In addition, the existing lead(Pb)-contained versions of products may be produced in parallel with the Lead(Pb)-Free versions of products, in consideration of various conditions you might have.

I hope the attached materials that describe our plan for Lead(Pb)-Free semiconductors are helpful. If you have any questions, please feel free to contact us through your sales representative. We look forward to your continued support and patronage.

Respectfully yours, Yoichi Takakubo Director, Quality Assurance Toshiba America Electronic Components, Inc.

1. Lead(Pb)-Free* Regulations and Global Trends

(1) Regulations

Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the use of certain hazardous substances in electrical and electronic equipment (the "RoHS Directive") will restrict use of lead(Pb), mercury (Hg), cadmium (Cd), hexavalent chromium (Cr⁶⁺) and PBB/PBDE from July 2006.

(2) Global Trends

Table 1-1 Global Lead(Pb)-Free Trends

EU	Legislated RoHS Directive. Lead(Pb) use will be restricted beginning in July 2006.
Japan	Corporations propose to enhance competitive edge through voluntary compliance with Lead(Pb)-Free standards. Various electronic products using Lead(Pb)-Free solder have been manufactured and are available in Japan
US	Regulations similar to those in the EU are being proposed and adopted in various jurisdictions. Moreover, the Lead(Pb)-Free trend is accelerated by major customers from the Lead(Pb)-Free movement in EU.

*Toshiba Semiconductor Company defines "Lead(Pb)-Free" in accordance with current industry standards as containing no more than 0.1 percent lead(Pb) by weight in homogenous materials. This does not mean that Toshiba products that are labeled Lead(Pb)-Free are entirely free of lead(Pb).



2. Basic Philosophy for TOSHIBA Lead(Pb)-Free Memory Products

Shift to Lead(Pb)-Free Products

TOSHIBA completed Lead(Pb)-Free implementation for all memory products by the end of December 2003.

Toshiba plans to change main memory Products to Lead(Pb)-Free products.

We are working with customers to convert all memory shipments to Lead(Pb)-Free, with a goal of completing this transition by the end of 2005.

(1) Lead-Finish Plating Materials

Sn-Ag and Sn-Cu are selected as alternative solder plating materials for our Lead(Pb)-Free products.

(2) Lead(Pb)-Free Solder Ball Materials

Sn-Ag-Cu is selected as an alternative solder ball material for our Lead(Pb)-Free products.

(3) Part Numbers of Lead(Pb)-Free Products

Part numbers have been changed to distinguish Lead(Pb)-Free from the lead(Pb)-contained products.

Note: The plating and ball materials are subject to change due to technology improvements.

3. Identifying Lead(Pb)-Free Products

(1) Part Number

A letter of "G" is specified in a part number field of Lead(Pb)–Free packages to distinguish Lead(Pb)-Free products from lead(Pb)-contained products. (Except for some custom products. Please contact your TOSHIBA sales representatives for details.)

Table 3 Example of Part Number Comparison of Lead(Pb)-contained and
Lead(Pb)-Free Products

Products	Lead(Pb)-contained Part Number	Lead(Pb)-Free Part Number
NAND 128Mb TSOP	TC58DVM72A1 <u>FT</u> 00	TC58DVM72A1 <u>TG</u> 00
PSRAM 32Mb P-TFBGA	TC51WHM516A <u>XB</u> N	TC51WHM516A <mark>XG</mark> N

Note: underlined letters show the package type

(2) Packing Label

Lead(Pb)-Free marking is indicated in the outer box label as follows: Lead(Pb)-Free products: "Lead (Pb)-Free" Lead(Pb)-Free Finish products: "Lead (Pb)-Free Finish"



Fig 3 Location of Lead(Pb)-Free Marking

4. Definitions

(1) Lead(Pb)-Free Components

As discussed in the preceding pages, there are various regulations that will limit the use of lead(Pb) in products. As a result, the term "Lead(Pb)-Free" or "Pb-Free" has become a commonly used term to the electronics industry to designate products that are intended to satisfy the various regulations regarding lead(Pb). However, at present there is no legally established uniform standard for the level of lead(Pb) that be allowed in a product under the various regulations. Notwithstanding the lack of a uniform legal standard, the electronics industry has generally adopted a standard of no more than 0.1 percent by weight in Homogenous Materials**. Under these circumstances, Toshiba Semiconductor Company will define "Lead(Pb)-Free" in accordance with the industry standard as no more than 0.1 percent lead(Pb) by weight in Homogenous Materials. This does not mean that Toshiba semiconductor products that are labeled Lead(Pb)-Free are entirely free of lead(Pb).

During a transitional phase, in addition to Lead(Pb)-Free products (that contain no more than 0.1 percent lead(Pb) by weight) Toshiba Semiconductor Company will also offer products that have Lead(Pb)-Free terminals, which will be referred to as "Lead(Pb)-Free Finish". The Lead(Pb)-Free Finish products may contain greater than 0.1 percent lead(Pb) by weight in portions of the product other than the terminals.

**Toshiba Semiconductor Company defines "Homogenous Material" to mean a material that cannot be mechanically disjointed into different materials. The term "homogenous" is understood as "of uniform composition throughout," so examples of "Homogenous Materials" would be individual types of plastics, ceramics, glass, metals, alloys, paper, board, resins and coatings. Toshiba Semiconductor Company defines the term "mechanically disjointed" to mean that the materials can be, in principle, separated by mechanical actions such as unscrewing, cutting, crushing, grinding and abrasive processes.

4. Definitions(2) RoHS-Compatible***

Reduction of lead(Pb) to a level of no more than 0.1% by weight is considered to be one requirement of the RoHS Directive***. However, to be RoHS-Compatible, a device must not contain more than the specified maximum concentration value of any of the six regulated substances or fall within the scope of an exemption. Of the regulated substances, lead(Pb) is the most widely used in semiconductor manufacturing, which accounts for the greater emphasis on Lead(Pb)-Free materials than on the other regulated substances in the semiconductor industry.

***Toshiba Semiconductor Company defines "RoHS-Compatible" semiconductor products as products that either (i) contain no more than a maximum concentration value of 0.1% by weight in Homogenous Materials for lead(Pb), mercury, hexavalent chromium, polybrominated byphenyls (PBBs) and polybrominated diphenyl ethers (PBDEs) and no more than 0.01% by weight in Homogenous Materials for cadmium; or (ii) fall within one of the stated exemptions set forth in the Annex to the RoHS Directive.

****Toshiba Semiconductor Company defines the "RoHS Directive" as the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Table 4 Classification of Lead(Pb)-Free Parts

The "Lead(Pb)-Free Soldering Roadmap" published by the Japan Electronics and Information Technology Industries Association (JEITA) classifies products into the following phases in view of the heat resistance in packaging, types of component parts and materials. Toshiba Semiconductor Company has adopted this classification scheme.

Classification	Criteria
Parts that withstand Lead(Pb)-Free soldering temperature	Parts with the solder heat resistance to withstand the higher temperature soldering requirements for Lead(Pb)-Free manufacturing processes.
Parts with Lead(Pb)- Free terminals	The plating of the terminals to be fitted to the board and electrodes of the part should be Lead(Pb)-Free. However, it is acceptable for the other components and materials of the part to have greater than 0.1 percent lead(Pb) by weight.
Lead(Pb)-Free parts	All sections of the part, including internal connections and/or components and materials are Lead(Pb)-Free.

5. Lead(Pb)-Free Materials

Lead(Pb)-Free materials of main package are shown in Table 5.

Table 5 Lead(Pb)-Free Materials by Package Types

	Package			Lead	(Pb)-Free	Materia	ıl
Package	Appearance	Structure	Sn-Ag	Sn-Ag-Cu	Sn-Cu	Au	Description
SOP, TSOP	Treasurenter	Lead Plating	•				Sn-Ag or Sn-Cu Plating
LGA		Terminal Plating					Cu Nickel
BGA		Solder Ball					Sn-Ag-Cu Ball

Note: When more than two materials for Lead(Pb)-Free terminals are stated, the specification depends on the part type.

6. Product Status

6.1 Network FCRAM

Product	Capacity	Organization	Power	Design	Package	Part Number	ES	CS	MP	Part Number	ES	CS	MP
TTOUUCI	(bit)	Organization	(V)	(um)	T uckuge	(Lead(Pb)-Free)	LJ	05	IVII	(Current Product)	LJ	05	
	256M	32M x 8	2M x 8		TSOP II 66-P-400-0.65	TC 59LM 806C TG	-	July/05	July/05	TC 59LM 806C FT	-	Now	Now
	230101	16M x 16		0.175	1301 11 001 -400-0.03	TC 59LM 814C TG	-	July/05	July/05	TC 59LM 814C FT	-	Now	Now
	288M	16M x 18		130nm	P-BGA60-0917-1.00AZ	TC 59LM 818DM G	-	Now	TBD	TC 59LM818DMB	-	Now	Now
Network	200101	8M x 36	2.5	1301111	P-TFBGA144-1119-0.80BZ	TC 59LM 836DKG	-	Now	TBD	TC 59LM 836DKB	-	Now	Now
FCRAM		64M x 8	2.5			TC 59LM 905AMG	-	TBD	TBD	TC 59LM 905AMB	-	TBD	TBD
	512M	32M x 16		130nm	P-BGA64-1317-1.00AZ	TC 59LM 913AMG	-	TBD	TBD	TC 59LM 913AMB	-	Now	Now
	012101	64M x 8		1001111		TC 59LM 906AMG	-	Now	Now	-			
		32M x 16				TC 59LM 914AMG	1	TBD	TBD	-			

6.2 SRAM(1)

Product	Capacity	Organization	Power	Design	Package	Part Number	ES	CS	MP	Part Number	ES	CS	MP
FTOULCE	(bit)	Organization	(V)	(um)	r ackaye	(Lead(Pb)-Free)	LJ	05	IVIT	(Current Product)	LJ	03	IVIE
			5		SOP32-P-525-1.27	TC 55N EM 208A FGN	-	Now	Now	TC 55N EM 208A FPN	-	Now	Now
					TSOP II 32-P-400-1.27	TC 55N EM 208A TG N	-	Now	Now	TC 55N EM 208AFTN	-	Now	Now
		512K x 8	2.7-5.5		SOP32-P-525-1.27	TC 55N EM 208A FG V	-	Now	Now	TC 55N EM 208A FPV	-	Now	Now
					TSOP II 32-P-400-1.27	TC 55N EM 208ATGV	-	Now	Now	TC 55N EM 208AFTV	-	Now	Now
			3.3		TSOP I 40-P-1014-0.50	TC55VCM208ASGN	-	Now	Now	TC 55VC M 208A STN	-	Now	Now
SRAM	4M			0.15	TSOP I 32-P-0.50	TC55VEM208ASGN	-	Now	Now	TC 55V EM 208A STN	-	Now	Now
			5		TSOP II 54-P-400-0.80	TC 55N EM 216A TGN	-	Now	Now	TC 55N EN 216A FTN	-	Now	Now
			2.7-5.5			TC 55N EN 216A TG V	-	Now	Noe	TC 55N EN 216A FTV	-	Now	Now
		256K x 16			TSOP II 44-P-400-0.80	TC 55N EM 216A SGV	-	Now	Now	TC 55N EM 216A STV	-	Now	Now
			3.3		TSOP I 48-P-1214-0.50	TC55VCM216ASGN	-	Now	Now	TC 55VC M216ASTN	-	Now	Now
					P-TFBGA48-0608-0.75BZ	TC55VEM216AGXN	-	Now	Now	TC55VEM216ABXN	-	Now	Now
			1.8			TC55YEM216AGXN	-	Now	Now	TC55YEM216ABXN	-	Now	Now

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SRAM(2)

C apacity	Organization	Power	Design	Package	Part Number	ES	CS	MP	Part Number	ES	CS
(bit)	Organization	(V)	(um)	T ackage	(Lead(Pb)-Free)	LJ	00		(Current Product)	LJ	00
	1M x 8/512K x 16		0.15	TSOP I 48-P-1220-0.50	-				TC 55VBM 316AFTN	-	Now
	512K x 16		0.13		TC 55VC M 316BTGN	-	Now	Jun./05	-		
	1M x 8/512K x 16	3.3	0.15	TSOP I 48-P-1214-0.50	TC 55VBM 316ASGN	-	Now	Now	TC 55VBM 316ASTN	-	Now
8M			0.13		TC55VCM316BSGN	-	Now	Jun./05	-		
			0.15	P-TFBGA48-0811-0.75BZ	TC 55VEM 316AXGN	-	Now	Now	-		
	512K x 16		0.13	P-TFBGA48-0607-0.75AZ	TC 55VEM 316BXGN	-	Now	Jun/05	-		
		1.8	0.15	P-TFBGA48-0811-0.75BZ	TC 55YEM 316AXGN	-	Now	Now	-		
			0.13	P-TFBGA48-0607-0.75AZ	TC 55YEM 316BXGN	-	Now	TBD	-		
	2M x 8/1M x 16		0.15	TSOP I 48-P-1220-0.50	TC55VBM416ATGN				TC55VBM416AFTN	-	Now
			0.13		TC 55VC M416BTGN	-	Now	Now	-		
		3.3		TSOP I 48-P-1214-0.50	TC55VCM416BSGN	-	Now	Now	-		
16M	1M x 16		0.15		TC 55VEM 416AXGN	-	Now	Now	-		
			0.13	P-TFBGA48-0811-0.75BZ	TC55VEM416BXGN	-	Now	Now	-		
		1.8	0.15		TC55YEM416AXGN	-	Now	Now	-		
			0.13		TC 55Y EM 416 BXGN	-	Now	TBD	-		

6.3 PSRAM

Product	Capacity	Organization	Power	Design	Package	Part Number	ES	CS	MP	Part Number	ES	CS	MP
Troduct	(bit)	organization	(V)	(um)	T dekage	(Lead(Pb)-Free)	LJ	00	IVII	(Current Product)	LJ	00	IVII
	32M	2M x 16			P-TFBGA48-0607-0.75AZ	TC51WHM516AXGN	-	Now	Now	TC51WHM516AXBN	Now	Now	Now
						TC51WKM516AXGN	-	Now	Now	TC51WKM516AXBN	Now	Now	Now
PSRAM	64M	4M x 16	2.7	0.175	P-TFBGA48-0811-0.75BZ	TC51WHM616AXGN	-	Now	Now	TC51WHM616AXBN	Now	Now	Now
						TC51WKM616AXGN	-	Now	Now	TC51WKM616AXBN	Now	Now	Now
	128M	8M x 16			P-FBGA69-0912-0.80B3	TC51WHM716AXGN	-	Now	Now	TC51WHM716AXBN	Now	Now	Now
						TC51WKM716AXGN	-	Now	Now	TC51WKM716AXBN	Now	Now	Now

6.4 NOR Flash

Product	Capacity	Organization	Power	Design	Package	Part Number	ES	CS	MP	Part Number	ES	CS	MP
TTOUUCI	(bit)	Organization	(V)	(um)	i ackage	(Lead(Pb)-Free)	LJ	05	IVII	(Current Product)	LJ	05	IVII
					TSOP I 48-P-1220-0.50	TC 58FVM 5T2ATG	Now	Now	Now	TC 58FVM 5T2AFT	Now	Now	Now
	32M	4M x 8/2M x 16				TC 58FVM5B2ATG	Now	Now	Now	TC 58FVM5B2AFT	Now	Now	Now
					P-TFBGA56-0710-0.80AZ	TC 58FVM 5T2AXG	Now	Now	Now	TC 58FVM 5T2AXB	Now	Now	Now
						TC 58FVM 5B2AXG	Now	Now	Now	TC 58FVM 5B 2A XB	Now	Now	Now
NOR			3.3	0.15	TSOP I 48-P-1220-0.50	TC 58FVM 6T2ATG	Now	Now	Now	TC 58FVM6T2AFT	Now	Now	Now
Flash	64M	8M x 8/4M x 16				TC 58FVM6B2ATG	Now	Now	Now	TC 58FVM6B2AFT	Now	Now	Now
					P-TFBGA56-0710-0.80AZ	TC 58FVM6T2AXG	Now	Now	Now	TC 58FVM6T2AXB	Now	Now	Now
						TC 58FVM6B2AXG	Now	Now	Now	TC 58FVM6B2AXB	Now	Now	Now
	128M	16M x 8/8M x 16			TSOP I 48-P-1220-0.50	TC 58FVM 7T2ATG	Now	Now	Now	TC 58FVM 7T2AFT	Now	Now	Now
						TC 58FVM 7B 2ATG	Now	Now	Now	TC 58FVM 7B 2AFT	Now	Now	Now

6.5 NAND Flash

Product	Capacity	Block Size	Power	Design	Package	Part Number	ES	CS	MP	Part Number	ES	CS	MP
TTOUDOL	(bit)	DIOCK SIZE	(V)	(um)	T dekdye	(Lead(Pb)-Free)	23	00	IVII	(Current Product)	23	00	IVII
	128M			0.13		TC 58DVM72A1TG00	Now	Now	Now	TC 58DVM 72A 1FT00	Now	Now	Now
	256M	16KB				TC 58DVM82A1TG00	Now	Now	Now	TC 58DVM82A1FT00	Now	Now	Now
NAND	512M					TC 58DVM92A1TG00	Now	Now	Now	TC 58DVM92A1FT00	Now	Now	Now
Flash	1G		3.3		TSOP I 48-P-1220-0.50	TC 58DVG02A1TG00	Now	Now	Now	TC 58DVG02A1FT00	Now	Now	Now
						TC 58N VG0S 3ATG05	Now	Now	Now	TC 58N VG 0S 3A FT 05	Now	Now	Now
	2G	128KB				TH58NVG1S3ATG05	Now	Now	Now	TH58NVG1S3AFT05	Now	Now	Now
				90nm		TC 58N VG 1S 3B TG 00	Now	Now	Now	TC 58N VG 1S 3A FT00	Now	Now	Now

7. Precautions for Lead(Pb)-Free Soldering

(1) Various Lead(Pb)-Free solder materials are available in the market. Some examples are described in Fig 2-1.

It will be necessary to select soldering material carefully and confirm reliability and workmanship of Lead(Pb)-Free soldering before actual production.

Note: Melting Points are determined by representative value, which depends on composition ratio. Please consult solder vendor for details.

Melting Point Solidus/Compositions

	= 236 Sn-5Sb	High melting point
	– 227 Sn-0.7Cu	Mainly used for flow soldering
	- 221 Sn-3.5Ag	However higher solder strength compared to Sn-Pb, the range of mounting temperature is narrow
36.10	– 217 Sn-3Ag-0.5Cu	Generally used in Japan
Melting Point (°C)	– 199 Sn-9Zn	Melting point of Sn-Zn system is approximate to Sn-Pb. Care should be taken to wettability and oxidization
	– 190 Sn-8Zn-3Bi	Bi additives lower the melting point of solder
	– 189 Sn-7.5Bi-2Ag-0.5Cu	Bi additives lower the melting point of solder. Care should be taken to the compatibility with Sn-Pb plating component.
	– 183 Sn-37Pb	Conventional solder (eutectic)
	– 139 Sn-57Bi	Good wettability. Care should be taken to the compatibility with Sn-Pb plating component.

Fig 7-1 Characteristics of General Lead(Pb)-free Solder



(2) Generally, the soldering temperature of Lead(Pb)-Free solder is higher than that of lead(Pb)-contained solder.

Please ensure that the soldering temperature does not exceed maximum rated temperature of components.

Fig 2-2 shows the example of reflow temperature profile by the use of Lead(Pb)-Free paste (Sn-3Ag-0.5Cu) for your reference.

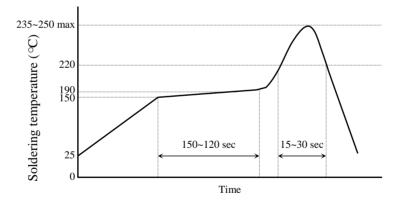


Fig 7-2 Example of Reflow Temperature Profile of Sn-3Ag-0.5Cu

8. Reflow Temperature Profile for Heat Resistance Test

Fig 8-1 shows the reflow temperature profile for heat resistance test of lead(Pb)-contained products and Fig 8-2 shows that of Lead(Pb)-Free products.

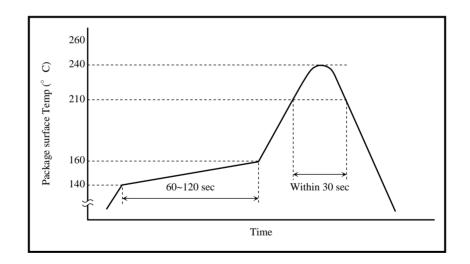


Fig 8-1 Reflow Temperature Profile for Heat Resistance Test of lead(Pb)contained Products

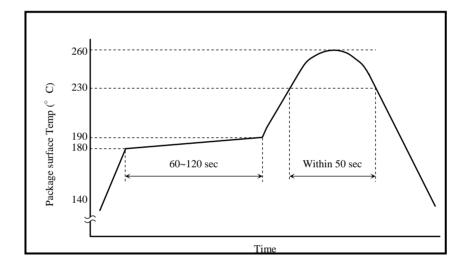


Fig 8-2 Reflow Temperature Profile for Heat Resistance Test of Lead(Pb)-Free Products

For further information, please visit <u>www.rohs.toshiba.com</u> or contact tech.questions@taec.toshiba.com.

Legal Note: The definitions included in this document for Lead(Pb)-Free and RoHS-Compatible and the related discussions are not intended to interpret the RoHS Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the use of certain hazardous substances in electrical and Electronic equipment (the "RoHS Directive") or any other law or regulation and do not constitute legal advice. The RoHS Directive itself should always be read and understood (as it constitutes the law), in contrast with the information contained herein, which is intended to be informative but has no legal authority. You should refer to the RoHS Directive itself for a full statement of the legal requirements and in the case of any doubt take independent advice, including your own legal advice. The RoHS Directive may be revised from time to time, so users should take care to keep themselves informed.

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The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.) These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.

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